PTO-1449

Atty. Docket No.

Serial No.

NMTI 1002-4

09/972,428-3974

Applicant

PIERRAT, Christophe

Filing Date

10/5/2001

Not Yet Assigned

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
JSR	4,037,918	7/26/1977	Kato	350	3.5	7/31/1975
1	4,456,371	6/26/1984	Lin	355	71	6/30/1982
	5,302,477	4/12/1994	Dao, et al.	430	5	8/21/1992
	5,308,741	5/3/1994	Kemp	430	312	7/31/1992
	5,316,878	5/31/1994	Saito, et al.	430	5	6/4/1992
	5,324,600	6/28/1994	Jinbo, et al.	430	5	7/7/1992
	5,328,807	7/12/1994	Tanaka, et al.	430	311	6/7/1991
	5,334,542	8/2/1994	Saito, et al.	437	40	11/18/1992
	5,352,550	10/4/1994	Okamoto	430	5	4/23/1993
	5,364,716	11/15/1994	Nakagawa, et al.	430	5	9/3/1992
	5,424,154	6/13/1995	Borodovsky	430	5	12/10/1993
	5,480,746	1/2/1996	Jinbo, et al.	430	5	5/16/1994
	5,496,666	3/5/1996	Chu, et al.	430	5	10/27/1994
	5,498,579	3/12/1996	Borodovsky, et al.	437	250	6/8/1994
	5,503,951	4/2/1996	Flanders, et al.	430	5	4/17/1995
	5,523,186	6/4/1996	Lin, et al.	430	5	12/16/1994
	5,527,645	6/18/1996	Pati, et al.	430	5	11/17/1994
	5,532,090	7/2/1996	Borodovsky	430	5	3/1/1995
	5,537,648	7/16/1996	Liebmann, et al.	395	500	8/15/1994
1	5,538,815	7/23/1996	Oi, et al.	430	5	9/14/1993
	5,539,568	7/23/1996	Lin, et al.	359	285	6/7/1995
	5,565,286	10/15/1996	Lin	430	5	11/17/1994
USP	5,573,890	11/12/1996	Spence	430	311	7/18/1994

EXAMINER:

Date Considered:

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

NTI Use Only: 747CON2; 52; 1

PTO-1449

Atty. Docket No.

Serial No.

NMTI 1002-4

09/972,428-3974

Applicant

PIERRAT, Christophe

Filing Date

Group

2824

10/5/2001

Not Yet Assigned-

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
OSR	5,595,843	1/21/1997	Dao	430	5	3/30/1995
	5,620,816	4/15/1997	Dao	430	5	10/13/1995
	5,635,316	6/3/1997	Dao	430	5	10/13/1995
	5,636,131	6/3/1997	Liebmann, et al.	364	490	5/12/1995
	5,702,848	12/30/1997	Spence	430	5	8/23/1996
	5,725,969	3/10/1998	Lee	430	5	12/22/1995
	5,761,075	6/2/1998	Oi, et al.	364	488	5/31/1996
1	5,766,804	6/16/1998	Spence	430	5	8/23/1996
	5,766,806	6/16/1998	Spence	430	5	9/9/1996
	5,807,649	9/15/1998	Liebmann, et al.	430	5	10/31/1996
	5,827,623	10/27/1998	Ishida, et al.	430	5	10/30/1996
	5,858,580	1/12/1999	Wang, et al.	430	5	9/17/1997
	5,885,734	3/23/1999	Pierrat, et al.	430	5	8/15/1996
	5,923,566	6/13/1999	Galan, et al.	364	489	3/25/1997
	5,994,002	11/30/1999	Matsuoka	430	5	9/4/1997
	5,998,068	12/7/1999	Matsuoka	430	5	1/27/1998
	6,004,702	12/21/1999	Lin	430	5	5/21/1998
	6,010,807	1/4/2000	Lin	430	5	4/7/1998
	6,057,063	5/2/2000	Liebmann, et al.	430	5	4/14/1997
	6,066,180	5/23/2000	Kim, et al.	716	19	3/15/1999
	6,077,630	6/20/2000	Pierrat	430	5	1/8/1998
	6,083,275	7/4/2000	Heng, et al.	716	19	1/9/1998
osn	6,228,539 B1	5/8/2001	Wang, et al.	430	5	1/12/1999

EXAMINER:

Date Considered:

5/8/03

7/17/2000

Atty. Docket No. Serial No. NMTI 1002-4 09/972,428-3974 INFORMATION DISCLOSURE **CITATION** Applicant PIERRAT, Christophe PTO-1449 Group Filing Date 10/5/2001 **U.S. PATENT DOCUMENTS** FILING CLASS SUBCLASS **EXAMINER'S** PATENT NO. DATE NAME DATE **INITIALS** 10/28/1999 430 11 6/26/2001 6,251,549 B1 Levenson

Wang, et al.

430

5

EXAMINER:

6,258,493 B1

7/10/2001

Date Considered:

			Atty. Docket No.	Seria	ıl No.		
INFORMATION DISCLOSURE		NMTI 1002-4	09	9/972,428-3974	ļ		
CITATION PTO-1449			Applicant PIERRAT, Christo	nhe			
			Filing Date	Group	2824	d	
					ot retrissigne	u	
		FOF	REIGN PATENT DOCU	MENTS			
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSI	NO
TSR_	JP 6-67403	3/11/1994	JP			×	
	0 698 821	2/28/1996	EPO				
JSR	8-51068	2/20/1996	JP			×	
	2,638,561	4/25/1997	- Jp				0
	2,650,962	5/16/1997	JP			-8-	0
TSR	EP 0 464 492 A1	1/8/1992	EP				
	EP 0 653 679 A2	5/17/1995	EP				
	7-111528	2/14/1991	JP				
052	8-236317	9/6/1996	JP				
	10 133356	5/22/1998	Ţb		 		-
	11-143085	5/28/1999	JP				9
TSR	JP 62067547	3/27/1987	JP				
	DE 195 43 163 A1	6/3/1996	DE				-0

EXAMINER:

Jos

Date Considered:

PTO-1449

Atty. Docket No.

Serial No.

NMTI 1002-4

09/972,428-3974

Applicant

PIERRAT, Christophe

Filing Date

Froup 1824

10/5/2001

Not Yet Assigned

	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
EXAMINER'S INITIALS	CITATION
JER	Ackmann, P., et al., "Phase Shifting and Optical Proximity Corrections to Improve CD Control on Logic Devices in Manufacturing for Sub 0.35 um I-Line", Advance Micro Devices (8 pages).
	Matsuoka, K., et al., "Application of Alternating Phase-Shifting Mask to 0.16um CMOS Logic Gate Patterns", Matsushita Electric Ind. Co., Ltd. (9 pages).
	Spence, C., et al., "Detection of 60(degree) Phase Defects on Alternating PSMs", Advanced Micro Devices, KLA-Tencor, DuPont RTC (2 pages).
	Sugawara, M., et al., "Defect Printability Study of Attenuated Phase-Shifting Masks for Specifying Inspection Sensitivity", Sony Corporation, Kanagawa, Japan (16 pages).
	Schmidt, R., et al., "Impact of Coma on CD Control for Multiphase PSM Designs", AMD, ASML (11 pages).
	Erdmann, A., "Topography Effects and Wave Aberrations in Advanced PSM-Technology", Fraunhofer Institute of Integrated Circuits (11 pages).
	Granik, Y., et al., "CD Variation Analysis Technique and its Application to the Study of PSM Mask Misalignment", Mentor Graphics (9 pages).
	Hanyu, et al., "New Phase-Shifting Mask with Highly Transparent SiO2 Phase Shifters", Fujitsu Laboratories Ltd. (11 pages).
	Ishiwata, N., et al., "Fabrication of Phase-Shifting Mask", Fujitsu Limited (11 pages).
	Levenson, M., et al., "Phase Phirst! An Improved Strong-PSM Paradigm", M.D. Levenson Consulting, Petersen Advanced Lithography, KLA-Tencor (10 pages).
	Levenson, M., et al., "SCAA Mask Exposures and Phase Phirst Design for 110nm and Below", M.D. Levenson Consulting, Canon USA, Inc., JSR Microelectronics, Inc. (10 pages).
	Lin, B.J., "The Relative Importance of the Building Blocks for 193nm Optical Lithography", Linnovation, Inc. (12 pages).
1	McCallum, M., et al., "Alternating PSM Mask Performance - a Study of Multiple Fabrication Technique Results", International SEMATECH (6 pages).
TSN	Morikawa, Y., et al., "100nm-alt.PSM Structure Discussion for ArF Lithography", Dai-Nippon Printing Co., Ltd. (15 pages).

EXAMINER:

Date Considered:

PTO-1449

Atty. Docket No.

Serial No.

NMTI 1002-4

09/972,428-3974

Applicant

PIERRAT, Christophe

Filing Date

Group

7824

10/5/2001

Not Yet Assigned

	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
EXAMINER'S INITIALS	CITATION		
TER	Ozaki, T., et al., "A 0.15um KrF Lithography for 1Gb DRAM Product Using Highly Printable Patterns and Thin Resist Process", Toshiba Corporation (2 pages).		
USR	Rhyins, P., et al., "Characterization of Quartz Etched PSM Masks for KrF Lithography at the 100nm Node", Photronics, Inc., MIT Lincoln Lab, ARCH Chemicals, Finle Technologies, KLATencor Corp. (10 pages).		
	Ronse, K., et al., "Thin Film Interference Effects in Phase Shifting Masks Causing Phase and Transmittance Errors", IMEC (15 pages).		
TSR	Rosenbluth, A., et al., "Optimum Mask and Source Patterns to Print a Given Shape", IBM (17 pages).		
	Sakata, M., et al., "A Novel Radiaion Sensitive Spin-on-Glass Convertible into SiO2 and the Simple Fabrication Process Using It", Oki Electric Industry Co. Ltd. (3 pages).		
	Schmidt, R., et al., "Impact of Coma on CD Control for Multiphase PSM Designs", AMD, ASML (10 pages).		
	Sewell, H., et al., "An Evaluation of the Dual Exposure Technique", SVG Lithography Systems Inc. (11 pages).		
	Spence, C., et al., "Optimization of Phase-Shift Mask Designs Including Defocus Effects", AMD, Princeton University, Vecor Technologies Inc. (8 pages).		
	Suzuki, A., et al., "Multilevel Imaging System Realizing k1=3 Lithogrpahy", Canon Inc. (13 pages).		
	Vandenberghe, G., et al., "(Sub-)100nm Gate Patterning Using 248nm Alternating PSM", IMEC, Mentor Graphics (9 pages).		
	Fritze, M., et al., "100-nm Node Lithography with KrF?", MIT Lincoln Lab, Numberical Technologies, Photronics, Arch Chemicals (14 pages).		
	Fukuda, H., et al., "Patterning of Random Interconnect Using Double Exposure of Strong-Type PSMs", Hitachi Central Research Lab (8 pages).		
	Ferguson, R., et al., "Pattern-Dependent Correction of Mask Topography Effects for Alternating Phase-Shifting Masks", IBM Microelectronics, University of California Berkeley (12 pages).		
JSR	-Toublan, O., et al., "Phase and Transmission Errors Aware OPC Solution for PSM: Feasibility Demonstration", Mentor Graphics Corp. (7 pages).		

EXAMINER:

Date Considered:

5/8/03

PTO-1449

Atty. Docket No.

Serial No.

NMTI 1002-4

09/972,428-3974

Applicant

PIERRAT, Christophe

Filing Date

Group

2824

10/5/2001

Not Yet Assigned

	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
EXAMINER'S INITIALS	CITATION		
TSR	Yanagishita, Y., et al., "Phase-Shifting Photolithography Applicable to Real IC Patterns", Fujitsu Limited (11 pages).		
)	Levenson, M., et al., "Improving Resolution in Photolithography with a Phase-Shifting Mask", IEEE, Transactions On Electron Devices, Vol. ED-29, No. 12, pp. 1828-1836, December 1982.		
	Levenson, M., et al., "The Phase-Shifting Mask II: Imaging Simulations and Submicrometer Resist Exposures", IEEE Transactions on Electron Devices, Vol. ED-31, No. 6, pp. 753-763, June 1984.		
	IBM, "Method to Produce Sizes in Openings in Photo Images Smaller Than Lithographic Minimum Size", IBM Technical Disclosure Bulletin, Vol. 29, No. 3, p. 1328, august 1986.		
	Terasawa, T., et al., "0.3-Micron Optical Lithography Using a Phase-Shifting Mask", SPIE, Optical/Laser Microlithography II, Vol. 1088, pp. 25-33, March 1989.		
	Buraschi, M., et al., "Optical-Diffraction-Based Modulation of Photoresist Profile or Microlithography Applications", Optical Engineering, Vol. 28, No. 6, pp. 654-658, June 1989.		
	Nitayama, A., et al., "New Phase Shifting Mask with Self-Aligned Phase Sifters for a Quarter Micron Photolithography", IEDM, pp. 3.3.1-3.3.4, December 3-6, 1989.		
	Jinbo, H., et al., "0.2um or Less i-Line Lithography by Phase-Shifting-Mask Technology", IEEE, pp. 33.3.1-33.3.4 (1990).		
	Neureuther, A., "Modeling Phase Shifting Masks", SPIE, 10th Annual Symposium On Microlithography, Vol. 1496, pp. 80-85 (1990).		
	Toh, K., et al., "Chromeless Phase-Shifted Masks: A New Approach to Phase-Shifting Masks", BACUS - Tenth Annual Symposium on Microlithograpy, September 1990 (27 pages).		
	Yamanaka, T., et al., "A 5.9um2 Super Low Power SRAM Cell Using a New Phase-Shift Lithography", IEDM, pp. 18.3.1-18.3.4 (1990).		
	Nakagawa, K., et al., "Fabrication of 64m DRAM with I-Line Phase-Shift Lithography", IEDM, pp. 33.1.1-33.1.4 (1990).		
	Watanabe, H., et al., "Transparent Phase Shifting Mask", IEDM, pp. 33.2.1-33.2.4 (1990).		
USR_	Inokuchi, K., et al., "Sub-Quarter Micron Gate Fabrication Process Using Phase-Shifting-Mask for Microwave GaAs Devices", Extended Abstracts Of The 1991 Intl. Conference On Solid State Devices And Materials, Yokohama, Japan, pp. 92-94 (1991).		

EXAMINER:

Date Considered:

5/8/03

PTO-1449

Atty. Docket No.

Serial No.

NMTI 1002-4

09/972,428-3974

Applicant

PIERRAT, Christophe

Filing Date

Group

2824

10/5/2001

Not Yet Assigned

	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
XAMINER'S INITIALS	CITATION
TSP	Inokuchi, K., et al., "Sub-Quarter-Micron Gate Fabrication Process Using Phase-Shifting Mask for Microwave GaAs Devices", Japanese Journal Of Applied Physics, Vol. 30, No. 12B, pp. 3818-3821, December 1991.
	Jinbo, H., et al., "Improvement of Phase-Shifter Edge Line Mask Method", Japanese Journal Of Applied Physics, Vol. 30, No. 11B, pp. 2998-3003, November 1991.
	Kimura, T., et al., "Subhalf-Micron Gate GaAs Mesfet Process Using Phase-Shifting-Mask Technology", IEEE, GaAs IC Symposium, pp. 281-284 (1991).
	Wiley, J., et al., "Phase Shift Mask Pattern Accuracy Requirements and Inspection Technology", SPIE, Integrated Circuit Metrology, Inspection, And Process Control V, Vol. 1464, pp. 346-355 (1991).
	Burggraaf, P., "Four More Significant Japanese Advances in Phase Shfiting Technology", Semiconductor International, p. 16, December 1991.
	Kemp, K., et al., "Optimized Phase Shift Mask Designs for Real Devices", KTI Microlithography Seminar, pp. 67-75, October 14-15, 1991.
	Newmark, D., et al., "Phase-Shifting Mask Design Tool", SPIE - 11th Annual BACUS Symposium on Photmask Technology, Vol. 1604, pp. 226-235, September 25-27, 1991.
	Nolscher, C., et al., "Investigation of Self-Aligned Phase-Shifting Reticles by Simulation Techniques", SPIE - Optical/Laser Microlithography IV, Vol. 1463, pp. 135-150 (1991).
	Asai, S., et al., "High Performance Optical Lithography Using a Separated Light Source", J. Vac. Sci. Technol. B, Vol. 10, No. 6, pp. 3023-3026, November/December 1992.
	Jinbo, H., et al., "Application of Blind Method to Phase-Shifting Lithography", IEEE, 1992 Symposium On VLSI Technology Digest Of Technical Papers, pp. 112-113 (1992).
	Ohtsuka, H., et al., "Phase Defect Repair Method for Alternating Phase Shift Masks Conjugate Twin-Shifter Method", Jpn. J. Appl. Phys., Vol. 31, pp. 4143-4149 (1992).
	Pierrat, C., et al., "Phase-Shifting Mask Topography Effects on Lithographic Image Quality", IEEE, pp. 3.3.1-3.3.4 (1992).
	Watanabe, H., et al., "Detection and Printability of Shifter Defects in Phase-Shifting Masks II Defocus Characteristics", Jpn. J. Appl. Phys., Vol. 31, pp. 4155-4160 (1992).
JER	Burggraaf, P., "Lithography's Leading Edge, Part 1: Phase-Shift Technology and Part 2: I-Line and Beyond", Semiconductor International, pp. 43-47 and 52-56, February 1992.

EXAMINER:

J. Raggler

Date Considered:

PTO-1449

Atty. Docket No.

Serial No.

NMTI 1002-4

09/972,428-3974

Applicant

PIERRAT, Christophe

Filing Date

Group

2824

10/5/2001

Not Yet Assigned

	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
XAMINER'S INITIALS	CITATION
JSR	Hosono, K., et al., "A Novel Architecture for High Speed Dual Image Generation of Pattern Data for Phase Shifting Reticle Inspection", SPIE - Integrated Circuit Metrology, Inspection, and Process Control VI, Vol. 1673, pp. 229-235 (1992).
)	IBM, "Phase-Shift Mask Utilizing Silicon Oxy-Nitride as a Low Reflectivity Phase-Shift Layer", IBM Technical Disclosure Bulletin, Vol. 34, No. 10B, pp. 360-361, March 1992.
	Brunner, T., et al., "170nm Gates Fabricated by Phase-Shift Mask and Top Anti-Reflector Process", SPIE, Optical/Laser Microlithography VI, Vo. 1927, pp. 182-189 (1993).
	Brunner, T., "Rim Phase-Shift Mask Combined with Off-Axis Illumination: A Path to 0.5(lampda) / Numerical Aperture Geometries", Optical Engineering, Vol. 32, No. 10, pp. 2337-2343, October 1993.
	Lin, B.J., "Phase-Shifting Masks Gain an Edge", IEEE Circuits & Devices, pp. 28-35, March 1993.
	Liu, H.Y., et al., "Fabrication of 0.1um T-Shaped Gates by Phase-Shifting Optical Lithography", SPIE, Optical/Laser Microlithography VI, Vol. 1927, pp. 42-52 (1993).
	Nistler, J., et al., "Phase Shift Mask Defect Printability Analysis", Proceedings Of The Microlithography Seminar INTERFACE '93, OCG Microelectronic Materials, Inc., pp. 11-28 (1993).
	Rieger, M., et al., "System for Lithography Proximity Compensation", Precim Company, Portland, Oregon, September 1993 (28 pages).
	Ronse, K., et al., "Comparison of Various Phase Shift Strategies and Application to 0.35um ASIC Designs", SPIE - Optical/Laser Microlithography VI, Vol. 1927, pp. 2-16 (1993).
	Troccolo, P., et al., "Interferometric Measurement of Etch Depths in Phase Shift Masks", BACUS News, Vol. 9, Issue 6, pp. 1 & 4-6, June 1993.
	Watanabe, H., et al., "Phase-Shifting Lithography: Maskmaking and its Application", J. Vac. Sci. Technol. B, Vol. 11, No. 6, pp. 2669-2674, November/December 1993.
	Galan, G., et al., "Application of Alternating-Type Phase Shift Mask to Polysilicon Level for Random Logic Circuits", Jpn. J. Appl. Phys., Vol. 33, pp. 6779-6784 (1994).
	Mizuno, F., et al., "Practical Phase-Shifting Mask Technology for 0.3um Large Scale Integrations", J. Vac. Sci. Technol. B, Vol. 12, No. 6, pp. 3799-3803, November/December 1994.
JSR-	Nistler, J., et al., "Large Area Optical Design Rule Checker for Logic PSM Application", SPIE, Photomask And X-Ray Mask Technology, Vol. 2254, pp. 78-92 (1994).

EXAMINER:

Date Considered:

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include

PTO-1449

Atty. Docket No.

Serial No.

NMTI 1002-4

09/972,428-3974

Applicant

PIERRAT, Christophe

Filing Date

Group

2824

10/5/2001

Not Yet Assigned

	10/3/2001 From Tet Assigned			
	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION			
TSR	Pati, Y.C., et al., "Phase-Shifting Masks for Microlithography: Automated Design and Mask Requirements", J. Opt. Soc. Am., Vol. 11, No. 9, pp. 2438-2452, September 1994.			
)	Pierrat, C., et al., "A Rule-Based Approach to E-Beam and Process-Induced Proximity Effect Correction for Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).			
	Spence, C., et al., "Automated Determination of CAD Layout Failures Through Focus: Experiment and Simulation", SPIE, Vol. 2197, pp. 302-313 (1994).			
	Stirniman, J., et al., "Wafer Proximity Correction and Its Impact on Mask-Making", Bacus News, Vol. 10, Issue 1, pp. 1, 3-7, 10-12, January 1994.			
1	Waas, T., et al., "Automatic Generation of Phase Shift Mask Layouts", Microelectronic Engineering, Vol. 23, pp. 139-142 (1994).			
	Barouch, E., et al., "OPTIMASK: An OPC Algorithm for Chrome and Phase-Shift Mask Design", SPIE, Vo. 2440, pp. 192-206, February 1995.			
	Karklin, L., "A Comprehensive Simulation Study of the Photomask Defects Printability", SPIE, Vol. 2621, pp. 490-504 (1995).			
	Langston, J., et al., "Extending Optical Lithography to 0.25um and Below", Solid State Technology, pp. 57-64, March 1995.			
	Nagahiro, Y., "Improved Mask Technique for Photolithography Applied to 0.25um LSI - Improvement of Resolution, Pattern Correction, Exposure Area", Nikkei Microdevices, pp. 1-6, April 1995.			
	Okamoto, Y., et al., "A New Phase Shifting Mask Technology for Quarter Micron Photolithography", SPIE, Vol. 2512, pp. 311-318 (1995).			
	Pierrat, C., et al., "Required Optical Characteristics of Materials for Phase-Shifting Masks", Applied Optics, Vol. 34, No. 22, pp. 4923-4928, August 1, 1995.			
	Galan, G., et al., "Alternating Phase Shift Generation for Coplex Circuit Designs", SPIE, Vol. 2884, pp. 508-519, September 18-20, 1996.			
i	Kanai, H., et al., "Sub-Quarter Micron Lithography with the Dual-Trench Type Alternating PSM", SPIE, Vol. 2793, pp. 165-173 (1996).			
TSR	Ishiwata, N., et al., "Novel Alternating Phase Shift Mask with Improved Phase Accuracy", SPIE, Proceedings Of The 17th Annual Symposium On Photomask Technology And Management, Vol. 3236, pp. 243-249 (1997).			

EXAMINER:

). Rygles

Date Considered:

5/8/03

PTO-1449

Atty. Docket No.

Serial No.

NMTI 1002-4

09/972,428-3974

Applicant

PIERRAT, Christophe

Filing Date

Group

2824

10/5/2001

Not Yet Assigned

	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
XAMINER'S INITIALS	CITATION			
55R	Morimoto, H., et al., "Next Generation Mask Strategy - Technologies are Ready for Mass Production of 256MDRAM?", SPIE, Vol. 3236, pp. 188-189 (1997).			
1	Roman, B., et al., "Implications of Device Processing on Photomask CD Requirements", SPIE, Vol. 3236 (1997) (Abstract Only).			
	Ishida, S., et al., "Large Assist Feature Phase-Shift Mask for Sub-Quarter Micrometer Window Pattern Formation", SPIE, Vol. 3096, pp. 333-343 (1997).			
	Nakae, A., et al., "A Proprosal for Pattern Layout Rule in Application of Alternating Phase Shift Mask", SPIE, Vol. 3096, pp. 362-374 (1997).			
	Tsujimoto, E., et al., "Hierarchical Mask Data Design System (PROPHET) for Aerial Image Simulation, Automatic Phase-Shifter Placement, and Subpeak Overlap Checking", SPIE, Vol. 3096, pp. 163-172 (1997).			
	Yamamoto, K., et al., "Hierarchical Processing of Levenson-Type Phase Shifter Generation", Jpn. J. Appl. Phys., Vol. 36, Part 1, No. 12B, pp. 7499-7503, December 1997.			
-	Gordon, R., et al., "Design and Analysis of Manufacturable Alternating Phase-Shifting Masks", Bacus News, Vol. 14, Issue 12, pp. 1-9, December 1998.			
	Nara, M., et al., "Phase Controllability Improvement for Alternating Phase Shift Mask", Dai Nippon Printing Co., Ltd. (16 pages).			
	Petersen, J., et al., "Designing Dual-Trench Alternating Phase-Shift Masks for 140nm and Smaller Features Using 248-nm KrF and 193-nm ArF Lithography", Bacus News, Vol. 14, Issue 8, pp. 1 & 4-13, August 1998.			
	Fukuda, H., et al., "Determination of High-Order Lens Aberration Using Phase/Amplitude Linear Algebra", J. Vac. Sci. Technol. B, Vol. 17, No. 6, pp. 3318-3321, November/December 1999.			
	Fukuda, H., "Node-Connection/Quantum Phase-Shifting Mask: Path to Below 0.3um Pitch, Proximity Effect Free, Random Interconnects and Memory Patterning", J. Vac. Sci. Technol. B, Vol. 17, No. 6, pp. 3291-3295, November/December 1999.			
	Spence, C., et al., "Integration of Optical Proximity Correction Strategies in Strong Phase Shifters Design for Poly-Gate Layers", Bacus News, Vol. 15, Issue 12, pp. 1, 4-13, December 1999.			
	Kuo, C., et al., "Extension of Deep-Ultraviolet Lithography for Patterning Logic Gates Using Alternating Phase Shifting Masks" J. Vac. Sci. Technol. B, Vol. 17, No. 6, pp. 3296-3300, November/December 1999.			
JSR	Palmer, S., et al., "Dual Mask Model-Based Proximity Correction for High Perfomance 0.10um CMOS Process", The 44th International Conference on Electron, Ion and Photon Beam Technology and Nanofabrication Abstracts, pp. 18-19, May 30-June			

EXAMINER:

Date Considered:

d: 0/8/0

		Atty. Docket No.	Serial No.
INFORMATION DISCLOSURE		NMTI 1002-4	09/972,428-3974
	CITATION	Applicant	
		PIERRAT, Christop	ohe
	PTO-1449	Filing Date 10/5/2001	Group 2824 Not Yet Assigned
	OTHER ROCHMENTS	(Including Author Title	Data Boutinant Bases Etc.)
	<u> </u>	(Including Author, Thie,	Date, Pertinent Pages, Etc.)
EXAMINER'S INITIALS	CITATION		
TSL	Pierrat, C., "Investigation of Proximity Effects in Alternating Aperture Phase Shifting Masks", Numerical Technologies, Inc. (11 pages).		
	Cote, M., et al., "A Practical Application of Full-Feature Alternating Phase-Shifting Technology for a Phase-Aware Standard-Cell Design Flow", Numerical Technologies Inc. (6 pages).		
	Heng, F., et al., "Application of Automated Design Migration to Alternating Phase Sifht Mask Design", IBM Research Report RC 21978 (98769), February 26, 2001 (7 pages).		
TSR	Wong, A., et al., "Alternating Phase-Shifting Mask with Reduced Aberration Sensitivity: Lithography Considerations", Proc. SPIE, Vol. 4346, pp. 1-9 (2001).		

EXAMINER:

Date Considered:

TECHNOLOGY CENTER	AUG - 1 2002
ריו	002

At	ty.	Docket	No

Serial No.

INFORMATION DISCLOSURE CITATION

PTO-1449

NMTI 1002-4

09/972,428-3974

TATION Applicant

PIERRAT, Christophe

Filing Date

Group

10/5/2001

2824

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
V52	5,472,814	12/5/1995	Lin	430	5	11/17/1994
1	5,923,562	7/13/1999	Liebmann, et al.	364	488	10/18/1996
	6,130,012	10/10/2000	May, et al.	430	5	1/13/1999
	6,139,994	10/31/2000	Broeke, et al.	430	5	6/25/1999
	6,185,727 B1	2/6/2001	Liebmann	716	19	12/12/1995
	6,335,128 B1	1/1/2002	Cobb, et al.	430	5	9/28/1999
	6,338,922 B1	1/15/2002	Liebmann, et al.	430	5	5/8/2000
	2001/0000240 A1	4/12/2001	Wang, et al.	430	5	12/7/2000
TSN	2001/0028985 A1	10/11/2001	Wang, et al.	430	5	4/20/2001

EXAMINER:

Date Considered:

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

NT1 Use Only: 747CON2; 135; 1



PTO-1449

Atty. Docket No.

Serial No.

NMTI 1002-4

09/972,428-3974

Applicant

PIERRAT, Christophe

Filing Date

Group

10/5/2001

2824

FOREIGN PATENT DOCUMENTS

EXAMINER'S	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSI	LATION
INITIALS						YES	NO
TSR	WO 01/23961 A1	4/5/2001	wo				
	WO 02/03140 A1	1/10/2002	wo				
	JP 2-140743	5/30/1990	JP			×	
	GB 2,333,613 A	7/28/1999	GB				
OSK	WO 98/12605 A1	3/26/1998	wo				

1 AUG - 1 2002

EXAMINER:

Date Considered:

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance <u>and</u> not considered. Include copy of this form with next communication to applicant.

NTI Use Only: 747CON2; 135; 1

		Atty. Docket No.	Serial No.			
INFORMATION DISCLOSURE CITATION		NMTI 1002-4	09/972,428-	·397 £		
		Applicant		AL AL		
		PIERRAT, Christo	phe	Х50 - 9f		
	PTO-1449	Filing Date	99/972,428- ophe Group 2824	AUG - 1 2002		
		10/5/2001	2824			
	OTHER DOCUMENTS	(Including Author, Title,	, Date, Pertinent Pages	~		
EXAMINER'S INITIALS	CITATION					
OSR	Wang, R., et al., "Harined Phase Shift Ma Physical Design", Motorola Semiconducto		Advantages to Photolithography	Process and		
	Ogawa, K., et al., "Phase Defect Inspectio	n by Differential Interference", Lasc	ertee Corporation (12 pages).			
	Pistor, T., "Rigorous 3D Simulation of Ph pages).	ase Defects in Alternating Phase-Sh	ifting Masks", Panoramic Techn	nology Inc. (13		
	Semmier, A., et al., "Application of 3D EMF Simulation for Development and Optimization of Alternating Phase Shifting Masks", Infineon Technologies AG (12 pages).					
	Wong, A., et al., "Polarization Effects in Mask Transmission", University of California Berkeley (8 pages).					
	Hirai, Y., et al., "Automatic Pattern Gener of Technical Papers, pp. 95-96, May 28-3		sk", 1991 Symposium on VLSI	Technology, Digest		
	Wong, A., et al., "Investigating Phase-Shi	fting Mask Layout Issues Using a C	ad Toolkit", IEEE, pp. 27.4.1-2	7.4.4 (1991).		
	Terasawa, T., et al., "Imaging Characteris Applied Physics, Vol. 30, No. 11B, pp. 29		lftone Phase-Shifting Masks", Ja	apanese Journal of		
	Inoue, S., et al., "Simulation Study on Pha No. 11B, pp. 3010-3015, November 1991		erns", Japanese Journal of Appli	ed Physics, Vol. 30,		
	Watanabe, H., et al., "Detection and Printability of Shifter Defects in Phase-Shifting Masks", Japanese Journal of Applied Physics, Vol. 30, No. 11B, pp. 3016-3020, November 1991.					
	Watanabe, H., et al., "Pattern Transfer Characteristics of Transparent Phase Shifting Mask", Japanese Journal of Applied Physics, Vol. 30, No. 11B, pp. 3004-3009, November 1991.					
	Moniwa, A., et al., "Algorithm for Phase-1, No. 12B, pp. 5874-5879, December 11		Shifter Placement", Jpn. J. App.	. Phys., Vol. 32, Pt.		
	Ooi, K., et al., "Computer Aided Design S 12B, pp. 5887-5891, December 1993.	Software for Designing Phase-Shifting	ng Masks", Jpn. J. Appl. Phys.,	Vol. 32, Pt. 1, No.		
JSR	Ohtsuka, II., et al., "Evaluation of Repair No. 6, pp. 2665-2668, November/Decemb		se-Shift Mask", J. Vac. Sci. Tec	hnol. B, Vol. 11,		

EXAMINER:

Date Considered:

		Atty. Docket No.	Serial No.				
INFORMATION DISCLOSURE		NMTI 1002-4	09/972,428-3974				
	CITATION	Applicant					
		PIERRAT, Christophe					
	PTO-1449	Filing Date	Group				
		10/5/2001	2824				
	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
EXAMINER'S INITIALS							
TSR	Moniwa, A., et al., "Heuristic Method for Phase-Conflict Minimization in Automatic Phase-Shift Mask Design", Jpn. J. Appl. Phys., Vol. 34, Pt. 1, No. 12B, pp. 6584-6589, December 1995.						
	Ohnuma, H., et al., "Lithography Computer Aided Design Technology for Embedded Memory in Logic", Jpn. J. Appl. Phys., Vol. 37, Part I, No. 12B, pp. 6686-6688, December 1998.						
JSR	Kikuchi, K., et al., "Method of Expanding Process Window for the Double Exposure Technique with alt-PSMs", Optical Microlithography XIII, Proceeding of SPIE, Vol. 4000, pp. 121-131 (2000).						

TECHNOLOGY CENTER 2800

EXAMINER:

Date Considered:

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

NTI Use Only: 747CON2; 135; 2

PTO-1449

Atty. Docket No.

Serial No.

NMTI 1002-4

09/972,428

Applicant

PIERRAT, Christophe

C....

Filing Date

Group

10/5/2001

2824

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
JK	6,420,074 B2	7/16/2002	Wang et al.	430	5	12/7/2000
1	6,436,590 B2	8/20/2002	Wang, et al.	430	5	4/20/2001
	2002/0083410 Λ1	6/27/2002	Wu, et al.	716	19	12/5/2001
	2002/0122994 A1	9/5/2002	Cote, et al.	430	5	2/28/2002
	2002/0127479 A1	9/12/2002	Pierrat	430	5	2/6/2002
	2002/0129327 A1	9/12/2002	Pierrat, et al.	716	19	11/15/200
	2002/0136964 A1	9/26/2002	Pierrat	430	5	3/23/2001
	2002/0142231 A1	10/3/2002	Kling, et al.	430	5	4/25/2001
	2002/0142232 A1	10/3/2002	Kling, et al.	430	5	4/25/2001
	2002/0144232 A1	10/3/2002	Ma, et al.	716	21	5/31/2001
	2002/0152454 A1	10/17/2002	Cote, et al.	716	21	6/7/2002
TSR	2002/0155363 A1	10/24/2002	Cote, et al.	430	5	6/7/2002

EXAMINER:

Date Considered:

Atty. Docket No. Serial No. 09/972,428 NMTI 1002-4 INFORMATION DISCLOSURE **CITATION Applicant** PIERRAT, Christophe PTO-1449 Group Filing Date 10/5/2001 2824 FOREIGN PATENT DOCUMENTS COUNTRY TRANSLATION CLASS SUBCLASS EXAMINER'S PATENT NO. DATE YES INITIALS NO WO 02/073312 A1 9/19/2002 wo

EXAMINER:

Date Considered:

		Atty, Docket No.	Serial No.			
INFORMATION DISCLOSURE		NMTI 1002-4	09/972,428			
	CITATION	Applicant				
	DTO 1440	PIERRAT, Christophe				
	PTO-1449	Filing Date	Group			
		10/5/2001	2824			
,	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
EXAMINER'S INITIALS	CITATION					
USR	Cooke, M., "OPC/PSM Designs For Poly Gate Layers", European Semiconductor, Vol. 22, No. 7, pp. 57-59, July 2000.					
	Granik, Y., et al., "Sub-Resolution Process Windows And Yield Estimation Technique Based On Detailed Full-Chip CD Simulation", SPIE, Vol. 4182, pp. 335-341 (2000).					
	Plat, M., et al., "The Impact of Optical Enhancement Techniques on the Mask Error Enhancement Funchtion (MEEF)", SPIE, Vol. 4000, pp. 206-214, March 1-3, 2000.					
TSR	Mansuripur, M., et al., "Projection Photolithography", Optics & Photonics News 11, 17 pages, February 2000.					

FXAMINER:

Magle

Date Considered: